

# NEGF Method: Capabilities and Challenges

Supriyo Datta School of Electrical & Computer Engineering Purdue University



















**CNT Electronics** 









#### **Effective Mass Equation**

Finite Difference / Finite Element



Damle, Ren, Venugopal, Lundstrom ---> nanoMOS





#### Nanowire Electronics



Atomistic sp3d basis



Rahman, Wang, Ghosh, Klimeck, Lundstrom







Atomistic pz basis

lpha , eta are (2x2) matrices



#### Guo, Lundstrom





#### Nanowire/CNT Electronics



Atomistic

#### non-orthogonal basis



Siddiqui, Kienle, Ghosh, Klimeck





#### Molecular Electronics



#### Atomistic basis: Huckel / EHT / Gaussian

Ghosh, Rakshit,Liang, Zahid, Siddiqui, Golizadeh, Bevan, Kazmi



"Self-energy",  $\Sigma$ 





"Self-energy",  $\Sigma$ 





"Self-energy",  $\Sigma$ 



$$\begin{bmatrix} E - \varepsilon_1 - \frac{t^2}{E - \varepsilon_2} \end{bmatrix}$$



"Self-energy",  $\Sigma$ 







"Self-energy",  $\Sigma$ 









# **Bridging Disciplines**



## Basis mixing: Ghosh, Liang, Kienle, Polizzi



#### C60 on Silicon







#### **NEGF** equations



$$G = (ES - H - \Sigma)^{-1}$$
$$A = i [G - G^+]$$
$$\Gamma = i [\Sigma - \Sigma^+]$$

 $\begin{bmatrix} G^{n} \end{bmatrix} = \begin{bmatrix} G\Gamma_{1}G^{+} \end{bmatrix} f_{1} + \begin{bmatrix} G\Gamma_{2}G^{+} \end{bmatrix} f_{2}$   $\tilde{I} = \frac{q}{h} Trace \Gamma_{1} \begin{bmatrix} f_{1} \left[ A(E) \right] - \left[ G^{n}(E) \right] \end{bmatrix}$   $= \frac{q}{h} Trace \Gamma_{2} \begin{bmatrix} f_{2} \left[ A(E) \right] - \left[ G^{n}(E) \right] \end{bmatrix}$ 

# Matrices <--> Numbers



$$\begin{array}{l} \varepsilon & \longleftrightarrow & [H] \\ \gamma & \longleftrightarrow & [\Gamma], [\Sigma] \end{array} \end{array}$$

$$\mu \mathbf{1} \qquad \qquad \mathbf{1} \qquad \mathbf{1$$



#### Minimal Model



Nanowires / Nanotubes / Molecules



Drain current



Drain voltage

 $U = U_L + U_0(N - N_0)$ 









Method of moments: Jing Guo 3D Poisson solver: Eric Polizzi







Method of moments: Jing Guo 3D Poisson solver: Eric Polizzi

#### Correlations























-1.36



## Which LDA ?



## IP = E(N) - E(N-1)EA = E(N+1) - E(N)

Benzene

HOMO and LUMO

LDA

-1.36

1.64

LDA

-6.6



## N vs. μ





## N vs. $\mu$ : SCF Theory

 $U_i = U_0 \left( N - N_0 \right)$ 

Benzene



# Self-interaction Correction







#### N one-electron levels



#### 2<sup>N</sup> many electron levels





## Two choices



Works for  $\Gamma \geq U$ 

#### 2<sup>N</sup> many electron levels



Works for  $\Gamma << U$ 



#### Two choices





## What is a contact?





## What is a contact?





Energy has to be removed efficiently from the contacts: otherwise --> "hot" contacts







#### Venugopal, Lundstrom







#### Venugopal, Lundstrom







## Other "contacts"







## Other "contacts"





#### Molecular desorption?





## Hot "contacts"





#### Molecular desorption?







## Two choices





Works for  $\Gamma << U$ 



## Summary

**Unified Model** 



#### Electronics & Sensing



www.nanohub.org Electrical Resistance: An Atomistic View, Nanotechnology <u>15</u>, 5433 (2004)

Transients? Strong correlations ? "Hot contacts" ?



## Experiment vs. Theory



THEORY: Purdue Group (cond-mat/0403401) EXPT: Karlsruhe

Zahid, Paulsson, Ghosh